NSA5.0AT3G

400 Watt Peak Power Zener Transient Voltage Suppressor

Unidirectional

The NSA5.0AT3G is designed to protect voltage sensitive components from high voltage, high energy transients. It has excellent clamping capability, high surge capability, low zener impedance and a fast response time. The NSA5.0AT3G is ideally suited for use in communication systems, automotive, numerical controls, process controls, medical equipment, business machines, power supplies and many other industrial/consumer applications.

Features

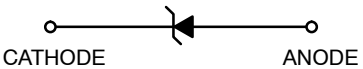
- Peak Power – 400 W @ 1 ms
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- ESD Rating IEC 61000–4–2 (> 30 kV)
- Response Time is Typically < 1 ns
- Flat Handling Surface for Accurate Placement
- Package Design for Top Slide or Bottom Circuit Board Mounting
- Low Profile Package
- Pb–Free Packages are Available

Mechanical Characteristics:
CASE: Void-free, transfer-molded plastic
FINISH: All external surfaces are corrosion resistant and leads are readily solderable
MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES: 260°C for 10 Seconds
POLARITY: Cathode indicated by molded polarity notch or polarity band
MOUNTING POSITION: Any

ON Semiconductor®

http://onsemi.com

PLASTIC SURFACE MOUNT ZENER OVERVOLTAGE TRANSIENT SUPPRESSOR 400 W PEAK POWER



SMA
CASE 403D
PLASTIC

MARKING DIAGRAM

QA = Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb–Free Package

ORDERING INFORMATION

Device	Package	Shipping†
NSA5.0AT3G	SMA (Pb–Free)	5000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DEVICE MARKING INFORMATION

See specific marking information in the device marking column of the Electrical Characteristics table on page 2 of this data sheet.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation (Note 1) @ T_L = 25°C, Pulse Width = 1 ms	P_{PK}	400	W
DC Power Dissipation @ T_L = 75°C Measured Zero Lead Length (Note 2) Derate Above 75°C Thermal Resistance from Junction to Lead	P_D $R_{\theta JL}$	1.5 20 50	W mW/°C °C/W
DC Power Dissipation (Note 3) @ T_A = 25°C Derate Above 25°C Thermal Resistance from Junction to Ambient	P_D $R_{\theta JA}$	0.5 4.0 250	W mW/°C °C/W
Forward Surge Current (Note 4) @ T_A = 25°C	I_{FSM}	40	A
Operating and Storage Temperature Range	T_J, T_{stg}	−65 to +150	°C

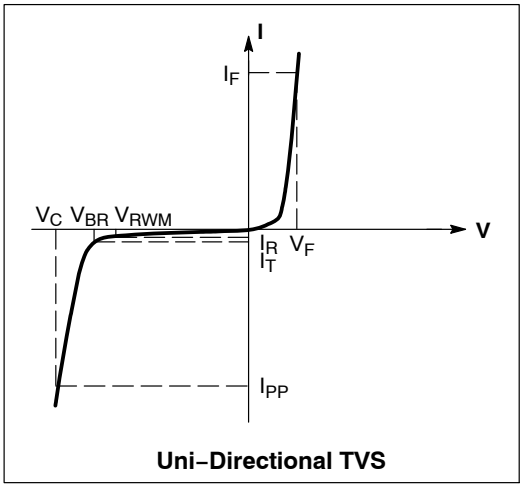
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. 10 X 1000 μs, non−repetitive.
2. 1″ square copper pad, FR−4 board.
3. FR−4 board, using ON Semiconductor minimum recommended footprint, as shown in 403D case outline dimensions spec.
4. 1/2 sine wave (or equivalent square wave), PW = 8.3 ms, duty cycle = 4 pulses per minute maximum.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_F	Forward Current
V_F	Forward Voltage @ I_F



Uni−Directional TVS

ELECTRICAL CHARACTERISTICS

Device	Device Marking	V_{RWM} (Note 5)	I_R @ V_{RWM}	Breakdown Voltage				V_C @ I_{PP} (Note 7)		C Typ. (Note 8)	V_F @ I_F (Note 9)
				V_{BR} (Volts) (Note 6)			@ I_T	V_C	I_{PP}		Max
		Volts	μA	Min	Nom	Max	mA	Volts	Amps	pF	V
NSA5.0AT3G	QA	5.0	400	6.4	6.7	7.0	10	9.2	43.5	2450	3.5

5. A transient suppressor is normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal to or greater than the DC or continuous peak operating voltage level.
6. V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C.
7. Surge current waveform per Figure 2 and derate per Figure 3.
8. Bias voltage = 0 V, F = 1.0 MHz, T_J = 25°C.
9. 1/2 sine wave or equivalent, PW = 8.3 ms, non−repetitive, I_F = 30 A.

RATING AND TYPICAL CHARACTERISTIC CURVES

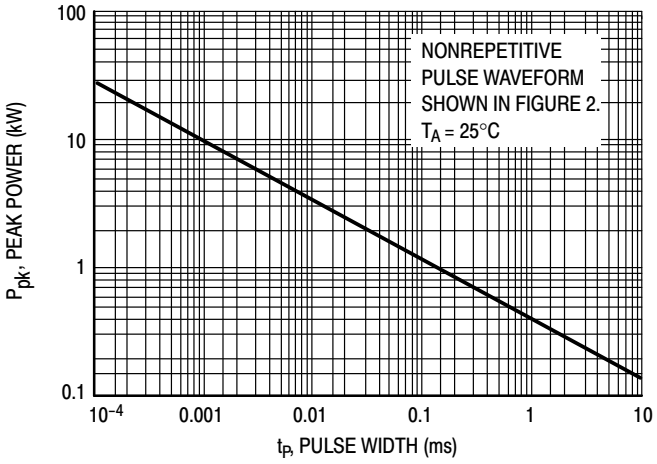


Figure 1. Pulse Rating Curve

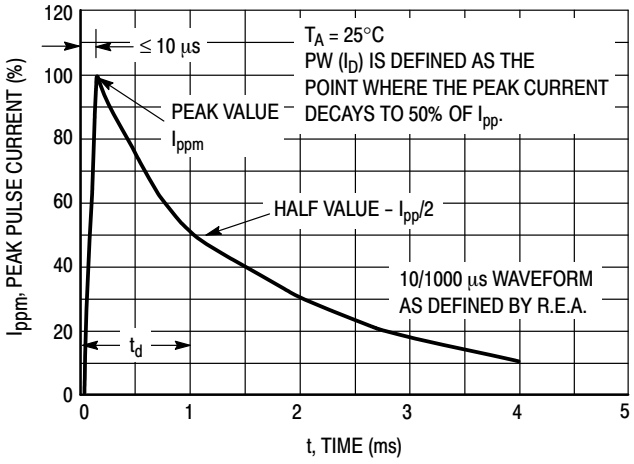


Figure 2. Pulse Waveform

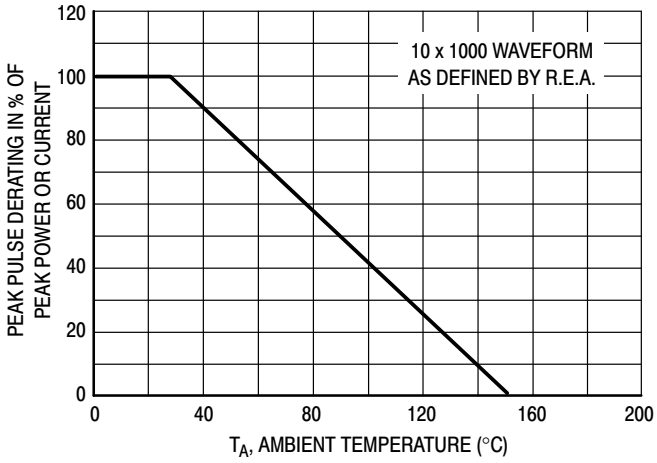


Figure 3. Pulse Derating Curve

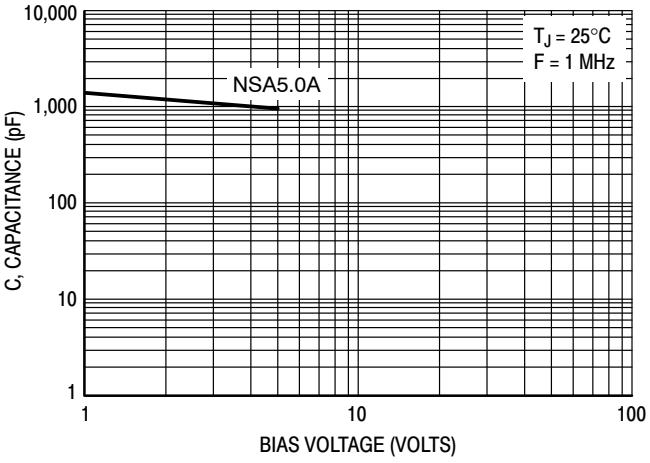


Figure 4. Typical Junction Capacitance vs. Bias Voltage

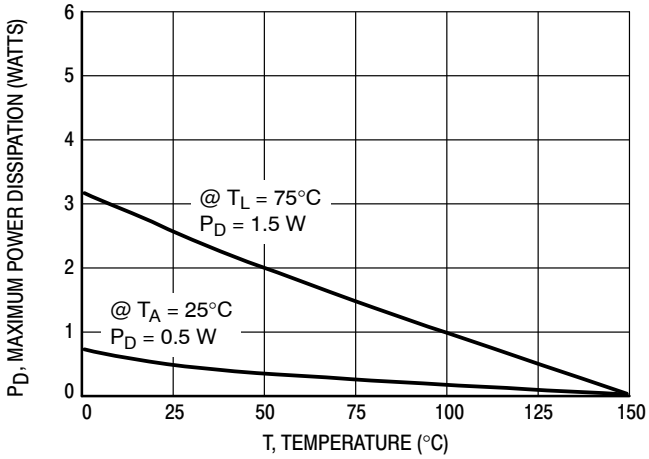
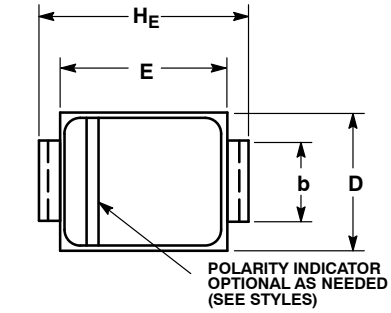
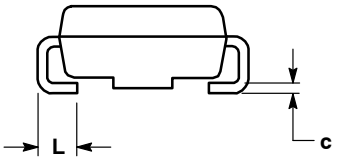


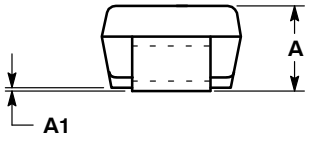
Figure 5. Steady State Power Derating

PACKAGE DIMENSIONS

SMA
CASE 403D−02
ISSUE E





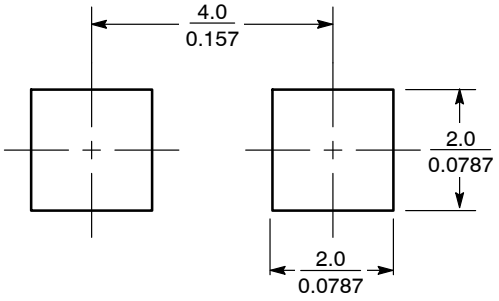


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 403D−01 OBSOLETE, NEW STANDARD IS 403D−02.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	1.97	2.10	2.20	0.078	0.083	0.087
A1	0.05	0.10	0.15	0.002	0.004	0.006
b	1.27	1.45	1.63	0.050	0.057	0.064
c	0.15	0.28	0.41	0.006	0.011	0.016
D	2.29	2.60	2.92	0.090	0.103	0.115
E	4.06	4.32	4.57	0.160	0.170	0.180
H_E	4.83	5.21	5.59	0.190	0.205	0.220
L	0.76	1.14	1.52	0.030	0.045	0.060

STYLE 1:
PIN 1. CATHODE (POLARITY BAND)
2. ANODE

SOLDERING FOOTPRINT*



SCALE 8:1 $\left(\frac{mm}{inches}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
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